

ABSTRACT

SEMICONDUCTOR STRUCTURE

A semiconductor structure includes a carrier, a first protective layer, a
5 second protective layer, and a third protective layer. A first surface of the
first protective layer comprises a first anti-stress zone. A first extension
line from a first bottom edge intersects with a second extension line from a
second bottom edge to form a first base point. A first projection line is
formed on the first surface, an extension line of the first projection line
10 intersects with the second bottom edge to form a first intersection point, a
second projection line is formed on the first surface, and an extension line of
the second projection line intersects with the first bottom edge to form a
second intersection point. A zone by connecting the first base point, the
first intersection point and the second intersection point is the first anti-stress
15 zone.

FIG. 3